imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconduc



November 2015

FOD814 Series, FOD817 Series 4-Pin DIP Phototransistor Optocouplers

Features

• AC Input Response (FOD814)

FOD814A: 50-150%

- Current Transfer Ratio in Selected Groups: FOD814: 20–300% FOD817: 50–600%
 - FOD817: 50–600% FOD817A: 80–160% FOD817B: 130–260% FOD817C: 200–400% FOD817D: 300–600%
- Minimum BV_{CEO} of 70 V Guaranteed
- Safety and Regulatory Approvals
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN EN/IEC60747-5-5

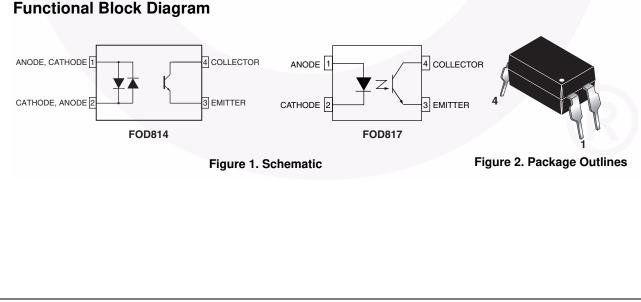
Applications

FOD814 Series

- AC Line Monitor
- Unknown Polarity DC Sensor
- Telephone Line Interface
- FOD817 Series
- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs

Description

The FOD814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a silicon phototransistor output in a 4-pin dual in-line package. The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.



Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification	30/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1560	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	8000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option W, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ _S	Case Temperature ⁽¹⁾	175	°C
I _{S,INPUT}	Input Current ⁽¹⁾	400	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	700	mW
R _{IO}	Insulation Resistance at T _S , $V_{IO} = 500 V^{(1)}$	> 10 ¹¹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ Unless otherwise specified.

Symbol	Devenetor	Va	lue	
Symbol	Parameter	FOD814	FOD817	Unit
Total Device				
T _{STG}	Storage Temperature	-55 to	o +150	°C
T _{OPR}	Operating Temperature	-55 to +105	-55 to +110	°C
Т _Ј	Junction Temperature	-55 to	o +125	°C
T _{SOL}	Lead Solder Temperature	260 for 1	0 seconds	°C
θ_{JC}	Junction-to-Case Thermal Resistance	2	10	°C/W
P _{TOT}	Total Device Power Dissipation	200		mW
EMITTER				
١ _F	Continuous Forward Current	±50	50	mA
V _R	Reverse Voltage		6	V
Р	Power Dissipation	70		mW
PD	Derate Above 100°C	1.7		mW/°C
DETECTOR				
V _{CEO}	Collector-Emitter Voltage	70		V
V _{ECO}	Emitter-Collector Voltage	6		V
۱ _C	Continuous Collector Current	5	50	mA
Р	Collector Power Dissipation	150		mW
P _C	Derate Above 90°C	2	2.9	mW/°C

Electrical Characteristics

 $T_A = 25^{\circ}C$ unless otherwise specified.

Individual Component Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit	
EMITTER				1				
	Forward Voltage	FOD814	$I_F = \pm 20 \text{ mA}$		1.2	1.4	v	
V_{F}		FOD817	I _F = 20 mA		1.2	1.4	v	
I _R	Reverse Current	FOD817	V _R = 4.0 V			10	μA	
0			V = 0, f = 1 kHz		50	250	~	
C _t T	Terminal Capacitance	FOD817	V = 0, f = 1 kHz		30	250	pF	
DETECTO	DR				•			
1	Collector Dark Current	FOD814	$V_{CE} = 20 \text{ V}, \text{ I}_{F} = 0$			100	nA	
ICEO	Collector Dark Current	FOD817	$V_{CE} = 20 \text{ V}, \text{ I}_{F} = 0$			100	na I	
	Collector-Emitter Breakdown	FOD814	$I_{\rm C} = 0.1 {\rm mA}, I_{\rm F} = 0$	70			v	
BV _{CEO}	Voltage	FOD817	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm F} = 0$	70				
	Emitter-Collector Breakdown	FOD814	$I_{E} = 10 \ \mu A, I_{F} = 0$	6			v	
BV _{ECO}	Voltage	FOD817	$I_{E} = 10 \ \mu A, I_{F} = 0$	6			V	

DC Transfer Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
		FOD814	I _F = ±1 mA, V _{CE} = 5 V	20		300	
		FOD814A	$r_F = \pm 1$ mA, $v_{CE} = 5$ v	50		150	
		FOD817		50		600	
CTR	Current Transfer Ratio ⁽²⁾	FOD817A		80		160	%
		FOD817B	$I_{F} = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	130		260	
		FOD817C		200		400	
		FOD817D		300		600	
V.	Collector-Emitter Saturation	FOD814	$I_F = \pm 20 \text{ mA}, I_C = 1 \text{ mA}$		0.1	0.2	v
V _{CE(SAT)}	Voltage	FOD817	$I_{F} = 20 \text{ mA}, I_{C} = 1 \text{ mA}$		0.1	0.2	v

AC Transfer Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
f _C	Cut-Off Frequency	FOD814		15	80	2	kHz
t _r	Response Time (Rise)	FOD814, FOD817	$V_{CE} = 2 \text{ V}, \text{ I}_{C} = 2 \text{ mA},$ $R_{I} = 100 \ \Omega^{(3)}$		4	18	μs
t _f	Response Time (Fall)	FOD814, FOD817	$R_{L} = 100 \ \Omega^{(3)}$		3	18	μs

Notes:

2. Current Transfer Ratio (CTR) = $I_C / I_F x 100\%$.

3. For test circuit setup and waveforms, refer to page 7.

Electrical Characteristics (Continued)

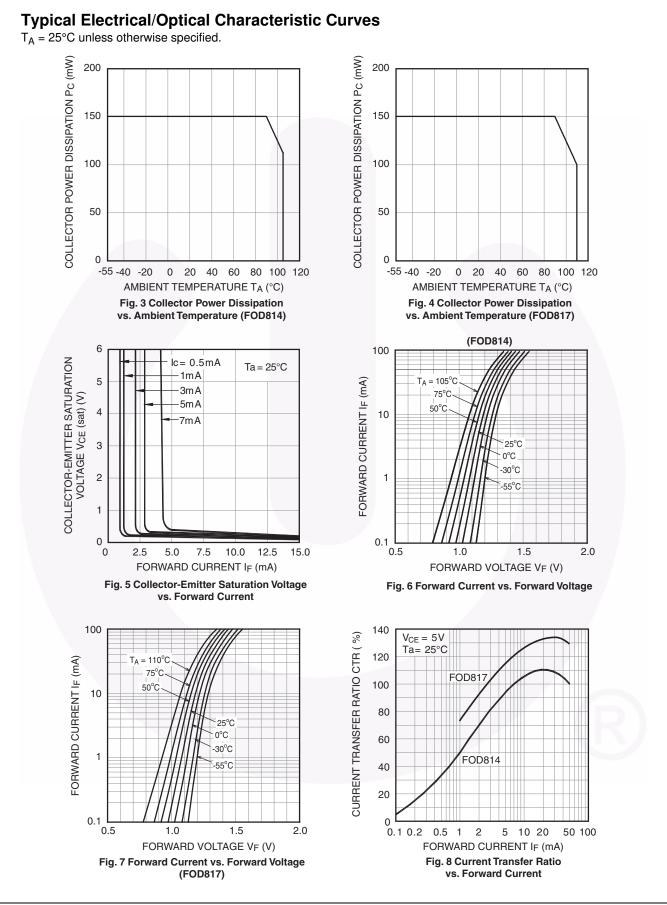
 $T_A = 25^{\circ}C$ unless otherwise specified.

Isolation Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage ⁽⁴⁾	FOD814, FOD817	$ f = 60 \text{ Hz}, t = 1 \text{ minute}, \\ I_{I-O} \le 2 \mu A $	5000			VAC _{RMS}
R _{ISO}	Isolation Resistance	FOD814, FOD817	V _{I-O} = 500 V _{DC}	5x10 ¹⁰	1x10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	FOD814, FOD817	V _{I-O} = 0, f = 1 MHz		0.6	1.0	pf

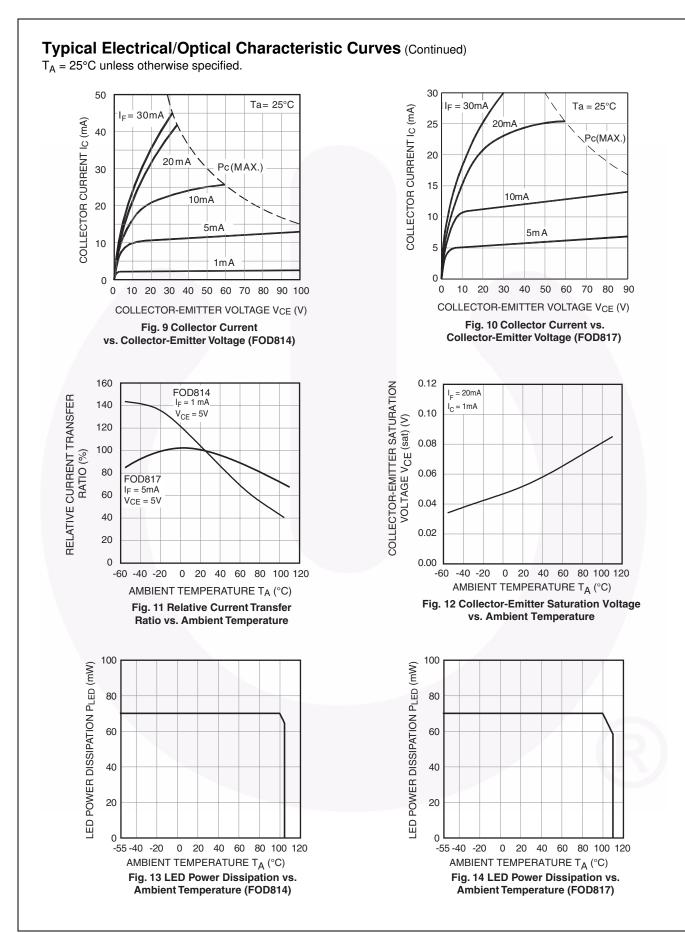
Note:

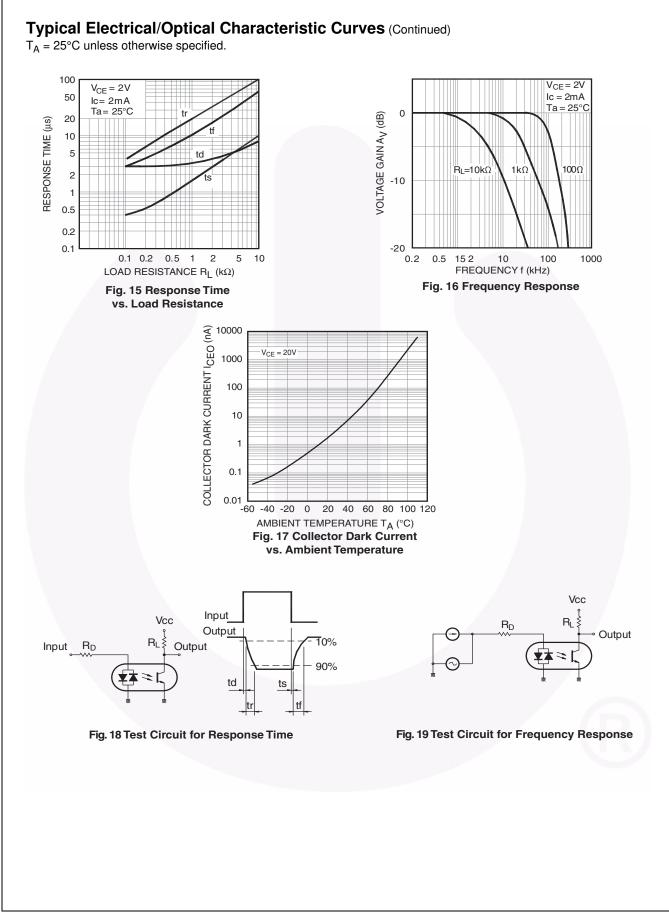
4. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

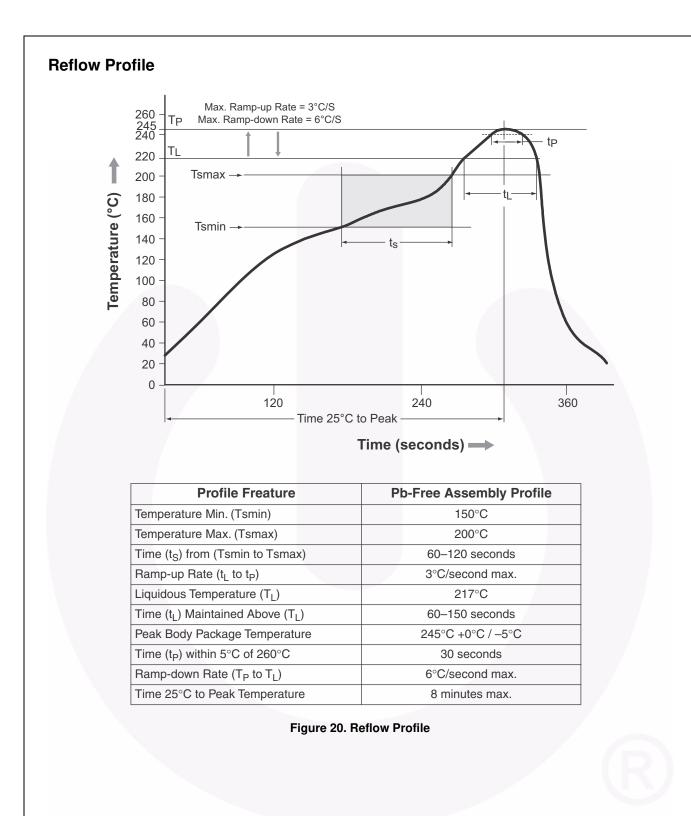


©2006 Fairchild Semiconductor Corporation FOD814 Series, FOD817 Series Rev. 2.8









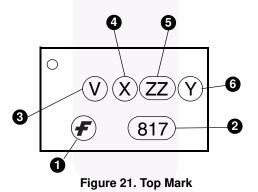
Ordering Information

Part Number	Package	Packing Method
FOD817X	DIP 4-Pin	Tube (100 units per tube)
FOD817XS	SMT 4-Pin (Lead Bend)	Tube (100 units per tube)
FOD817XSD	SMT 4-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
FOD817X300	DIP 4-Pin, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD817X3S	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD817X3SD	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tape and Reel (1,000 units per reel)
FOD817X300W	DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)

Note:

The product orderable part number system listed in this table also applies to the FOD814 products. "X" denotes the Current Transfer Ratio (CTR) options

Marking Information



Definiti	Definitions					
1	Fairchild Logo					
2	Device Number					
3	DIN EN/IEC60747-5-5 Option (only appears on parts ordered with this option)					
4	One-Digit Year Code, e.g., '5'					
5	Two-Digit Work Week, Ranging from '01' to '53'					
6	Assembly Package Code Y = Manufactured in Thailand YA = Manufactured in China					

Carrier Tape Specifications

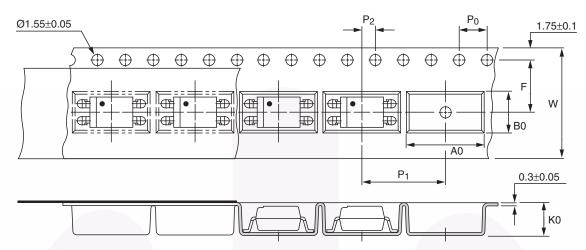
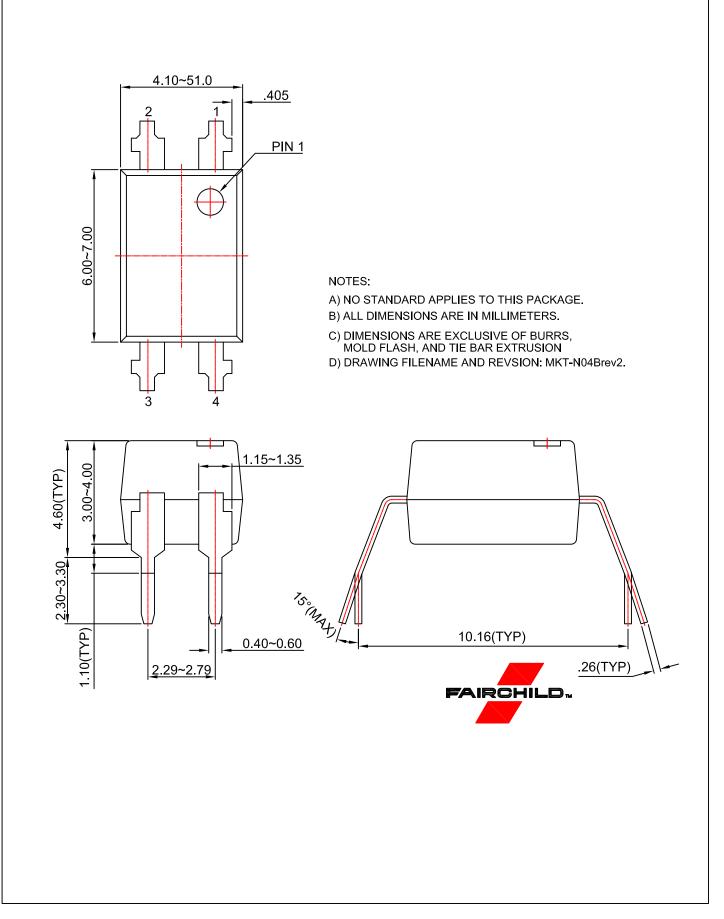
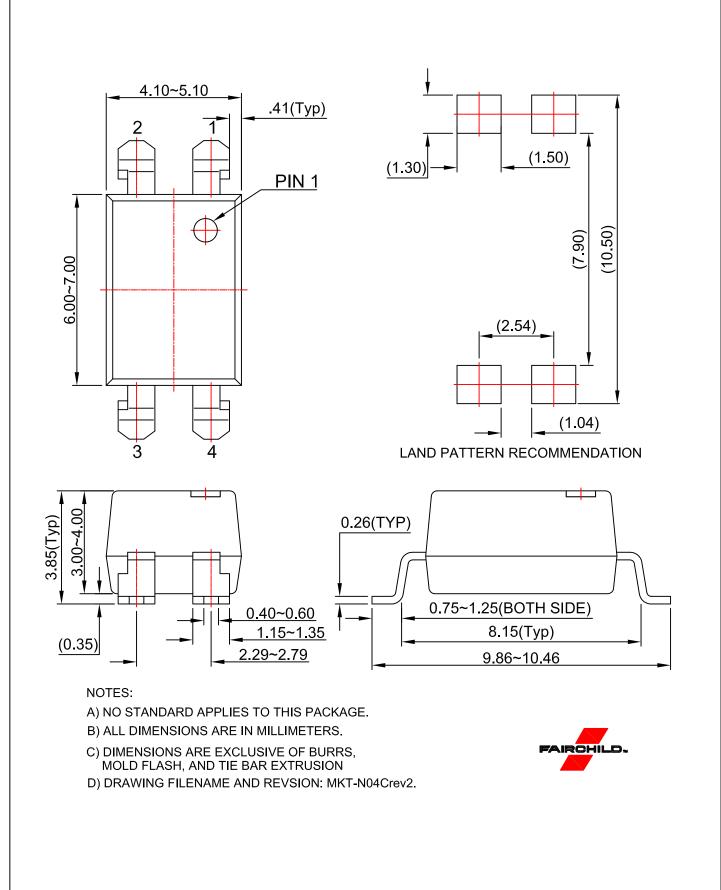
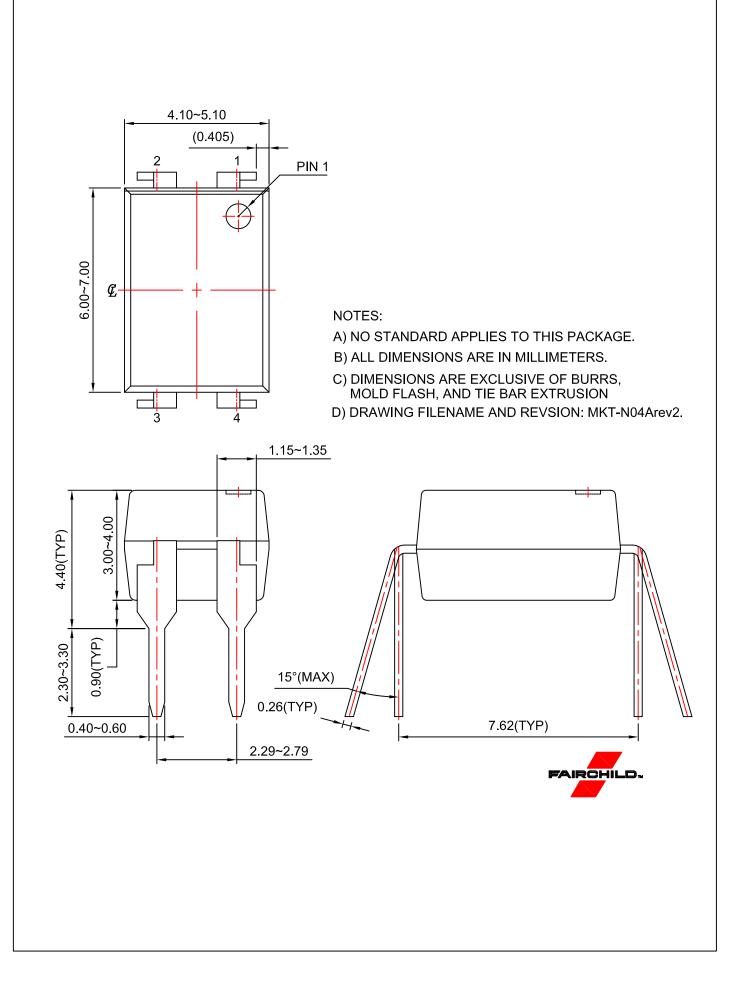


Figure 22. Carrier Tape Specification

Symbol	Description	Dimensions in mm (inches)
W	Tape wide	16 ± 0.3 (0.63)
P ₀	Pitch of sprocket holes	4 ± 0.1 (0.15)
F P ₂	Distance of compartment	7.5 ± 0.1 (0.295) 2 ± 0.1 (0.079)
P ₁	Distance of compartment to compartment	12 ± 0.1 (0.472)
A0	Compartment	10.45 ± 0.1 (0.411)
B0		5.30 ± 0.1 (0.209)
K0		4.25 ± 0.1 (0.167)







ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC